

Faculty of Engineering

End Semester Examination May 2025

EC3CO03 Electronic Devices & Circuits

Programme	:	B.Tech.	Branch/Specialisation	:	EC
Duration	:	3 hours	Maximum Marks	:	60

Note: All questions are compulsory. Internal choices, if any, are indicated. Assume suitable data if necessary. Notations and symbols have their usual meaning.

Section 1 (Answer all question(s))				Marks CO BL
Q1. The diffused impurities with _____ valence electrons are called donor atoms.				1 1 1
<input type="radio"/> 4		3		
<input checked="" type="radio"/> 5		2		
Q2. Schottky diodes are also known as-				1 1 1
<input type="radio"/> PIN diodes		<input checked="" type="radio"/> Hot carrier diodes		
<input type="radio"/> Step-recovery diodes		<input type="radio"/> Tunnel diodes.		
Q3. A transistor has a β_{DC} of 250 and a base current, I_B , of $20\mu A$. The collector current, I_C , equals:				1 2 1
<input type="radio"/> $500\mu A$		<input checked="" type="radio"/> 5 mA		
<input type="radio"/> 50mA		<input type="radio"/> 5A		
Q4. When transistors are used in digital circuits they usually operate in the:				1 2 1
<input type="radio"/> Active region		<input type="radio"/> Breakdown region		
<input checked="" type="radio"/> Saturation and cut off regions		<input type="radio"/> Linear region		
Q5. A JFET is also called _____ transistor.				1 3 1
<input checked="" type="radio"/> Unipolar		<input type="radio"/> Bipolar		
<input type="radio"/> Unijunction		<input type="radio"/> None of the above		
Q6. With the E-MOSFET, when gate input voltage is zero, drain current is:				1 3 1
<input type="radio"/> At saturation		<input checked="" type="radio"/> Zero		
<input type="radio"/> IDSS		<input type="radio"/> Widening the channel		
Q7. What should be the value of input resistance for an ideal voltage amplifier circuit?				1 4 1
<input type="radio"/> Zero		<input type="radio"/> Unity		
<input checked="" type="radio"/> Infinity		<input type="radio"/> Unpredictable		
Q8. Why is RC coupling confined to low power applications?				1 4 1
<input type="radio"/> Due to large value of coupling capacitor		<input checked="" type="radio"/> Low efficiency		
<input type="radio"/> Large number of components		<input type="radio"/> Due to is frequency response		
Q9. In an LC oscillator, the frequency of oscillator is _____ L or C.				1 5 1
<input type="radio"/> Proportional to square of		<input type="radio"/> Directly proportional to		
<input type="radio"/> Independent of the values of		<input checked="" type="radio"/> Inversely proportional to square root of		
Q10. Only the condition $\beta A = \dots$ must be satisfied for self-sustained oscillations to result.				1 5 1
<input checked="" type="radio"/> 1		<input type="radio"/> 0		
<input type="radio"/> -1		<input type="radio"/> None of the above		

Section 2 (Answer all question(s))

Marks CO BL

Q11. Define diffusion and drift current.

2 1 1

Rubric	Marks
Define diffusion current.	1
Define drift current.	1

Q12. Explain the Hall effect.

3 1 1

Q13. (a) Draw and explain the full wave center tapped rectifier circuit and also derive the expression for their efficiency.

5 2 1

Rubric	Marks
Draw and explain the full wave center tapped rectifier circuit.	2
For full wave center tapped rectifier circuit derive the expression for their efficiency.	3

(OR)

(b) Draw and explain the V I characteristic of Tunnel diode. Explain the tunnelling phenomenon.

Rubric	Marks
Draw the V I characteristic of Tunnel diode.	2
Explain the V I characteristic of Tunnel diode.	3

Section 3 (Answer all question(s))

Marks CO BL

Q14. Explain dc load line of transistor.

2 2 1

Q15. Derive relation between α , β and Y in transistor.

3 2 1

Q16. (a) Explain the input and output characteristics of transistor in CE configuration. Also explain the regions of operation.

5 2 1

(OR)

(b) Explain the h parameter model and find out input impedance, voltage gain and current gain in terms of h parameter.

Section 4 (Answer all question(s))

Marks CO BL

Q17. What is pinch off condition?

2 3 1

Q18. Write down the difference between BJT and FET. (any3)

3 3 2

Q19. (a) Explain the working principal of n channel JFET with their characteristics.

5 3 1

Rubric	Marks
Explain the working principal of n channel JFET .	2
Characteristics of n channel JFET .	3

(OR)

(b) Explain the working principal of n channel enhancement type MOSFET with their characteristics.

Rubric	Marks
Draw construction diagram of n channel Enhancement type MOSFET.	2
Explain n channel Enhancement type MOSFET the working principal with their characteristics.	3

Section 5 (Answer any 2 question(s))

Marks CO BL

Q20. With the help of circuit diagram and waveform explain the operation of class B push pull power amplifier. Calculate its maximum power efficiency. 5 3 3

Rubric	Marks
Circuit diagram a of class B push pull power amplifier.	2
Draw waveform explain the operation of class B push pull power amplifier.	3

Q21. Explain the working of darlington pair amplifier. Why bootstrapping is done? 5 4 3

Q22. Draw and explain the working of RC coupled amplifier. 5 4 1

Section 6 (Answer any 2 question(s))

Marks CO BL

Q23. Explain various feedback topologies. Also derive an expression for input and output resistance for any one them. 5 4 3

Q24. Explain the working of Hartley oscillators. Also derive an expression for frequency of oscillation. 5 5 3

Q25. Explain the concept of feedback. Which feedback is generally used and why? 5 5 3
